

## PUBLICATIONS

### A. Publications in International Journals and Reviews

- A.1** "Photoluminescence properties of porous silicon/fluorene dye composites ", Fakis, M., Zacharatos, F., Gianneta, V., Persephonis, P., Giannetas, V., Nassiopoulou, A.G., Materials Science and Engineering B, . Article in Press. 2009
- A.2** "Photoluminescence in the blue spectral region from fluorene molecules embedded in porous anodic alumina thin films on silicon", M. Fakis, V. Gianneta, P. Persephonis, V. Giannetas, A. G. Nassiopoulou, Optical Materials, Optical Materials, 31 (8), pp. 1184-1188, 2009
- A.3** "Effect of exciton migration on the light emission properties in silicon nanocrystal ensembles", Gardelis, S., Nassiopoulou, A.G., Vouroutzis, N., Frangis, N., Journal of Applied Physics, 105 (11), art. no. 113509, 2009 (Selected for the July 2009, Issue (vol. 8, issue 7) of Virtual Journal of Ultrafast Science, 2009)
- A.4** "Formation of porous anodic alumina templates in selected micrometer-sized areas on a Si substrate. Application for growing ordered Ti nanopillars", Gianneta, V., Huffman, M., Nassiopoulou, A.G., Physica Status Solidi (A) Applications and Materials, 206 (6), pp. 1309-1312, 2009
- A.5** "Highly ordered hexagonally arranged sub-200 nm diameter vertical cylindrical pores on p-type Si using non-lithographic pre-patterning of the Si substrate", Zacharatos, F., Gianneta, V., Nassiopoulou, A.G., Physica Status Solidi (A) Applications and Materials, 206 (6), pp. 1286-1289, 2009
- A.6** "Enhancement and red shift of photoluminescence (PL) of fresh porous Si under prolonged laser irradiation or ageing: Role of surface vibration modes", Gardelis, S., Nassiopoulou, A.G., Mahdouani, M., Bourguiga, R., Jaziri, S., Physica E: Low-Dimensional Systems and Nanostructures, 41 (6), pp. 986-989, 2009
- A.7** "Laterally ordered 2-D arrays of Si and Ge nanocrystals within SiO<sub>2</sub> thin layers for application in non-volatile memories", Nassiopoulou, A.G., Olzierski, A., Tsoi, E., Salonidou, A., Kokonou, M., Stoica, T., Vescan, L., International Journal of Nanotechnology, 6 (1-2), pp. 18-34 (2009)
- A.8** "RF characterization and isolation properties of mesoporous Si by on-chip coplanar waveguide measurements", H. Contopanagos, F. Zacharatos, A. G. Nassiopoulou, Solid-State Electronics, 52 (11), pp. 1730-1734 (2008)
- A.9** "Morphology, structure, chemical composition, and light emitting properties of very thin anodic silicon films fabricated using short single pulses of current", S. Gardelis, A. G. Nassiopoulou, F. Petraki, S. Kennou, I. Tsiaoussis, N. Frangis, Journal of Applied Physics, 103 (10), art. no. 103536 (2008)

- A.10** “Highly ordered hexagonally arranged nanostructures on silicon through a self-assembled silicon-integrated porous anodic alumina masking layer”, F. Zacharatos, V. Gianneta and A. G. Nassiopoulou, *Nanotechnology* 19, 495306 (2008)
- A.11** “Self-assembled hexagonal ordering of Si nanocrystals embedded in SiO<sub>2</sub> nanodots”, A. G. Nassiopoulou, V. Gianneta, M. Huffman, M. A. Reading, J. A. Van Den Berg, I. Tsiaoussis, N. Frangis, *Nanotechnology* 19, 495605 (2008)
- A.12** “Columnar growth of ultra-thin nanocrystalline Si films on quartz by Low Pressure Chemical Vapor Deposition: Accurate control of vertical size”, Lioutas, Ch.B., Vouroutzis, N., Tsiaoussis, I., Frangis, N., Gardelis, S., Nassiopoulou, A.G., *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2615-2620 (2008)
- A.13** “Growth and electrical characterization of thin conductive Au nanoparticle chains on oxidized Si substrates between electrodes for sensor applications”, A. Zoy, A. G. Nassiopoulou, *Phys. Status Solidi (A) Applications and Materials*, 205 (11), pp. 2621-2624 (2008)
- A.14** “Broadband electrical characterization of macroporous silicon at microwave frequencies”, H. Contopanagos, D. N. Pagonis, A. G. Nassiopoulou, *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2548-2551 (2008)
- A.15** “A thermal vacuum sensor fabricated on plastic substrate - Study in various operation modes”, A. Petropoulos, G. Kaltsas, A. G. Nassiopoulou, *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2639-2642 (2008)
- A.16** “Auger recombination in silicon nanocrystals embedded in SiO<sub>2</sub> wide band-gap lattice”, M. Mahdouani, R. Bourguiga, S. Jaziri, S. Gardelis, A. G. Nassiopoulou, *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2630-2634 (2008)
- A.17** “Copper-filled macroporous Si and cavity underneath for microchannel heat sink technology”, F. Zacharatos, A. G. Nassiopoulou, *Physica Status Solidi (A) Applications and Materials*, 205 (11), pp. 2513-2517 (2008)
- A.18** “Enhancement and red shift of photoluminescence (PL) of fresh porous Si under prolonged laser irradiation or ageing: Role of surface vibration modes“, S. Gardelis, A. G. Nassiopoulou, M. Mahdouani, R. Bourguiga, S. Jaziri, *Physica E: Low-Dimensional Systems and Nanostructures*, doi:10.1016/j.physe.2008.08.021(2008)
- A.19** “Surface-related states in oxidized silicon nanocrystals enhance carrier relaxation and inhibit auger recombination”, A. Othonos, E. Lioudakis, A. G. Nassiopoulou, *Nanoscale Research Letters*, 3 (9), pp. 315-320 (2008) and selected for open-access presentation to the OAtube *Nanotechnology* 1 (2008) 903
- A.20** “Determination of critical points on silicon nanofilms: surface and quantum confinement effects”, E. Lioudakis, A. Othonos and A. G. Nassiopoulou, *Phys. Stat. Sol. (c)*, 5 (2008) 3776
- A.21** “Multilevel charge storage in Si nanocrystals arranged in double-dot-layers within SiO<sub>2</sub>”, M. Theodoropoulou, A. G. Nassiopoulou, *Microelectronic Engineering* 85 (12), pp. 2362-2365 (2008)
- A.22** “Ultrafast time-resolved spectroscopy of Si nanocrystals embedded in SiO<sub>2</sub> matrix”, E. Lioudakis, A. Emporas, A. Othonos, A. G. Nassiopoulou, *Journal of Alloys and Compounds*, doi:10.1016/j.jallcom.2008.07.193, Article in Press (2008)

- A.23** "Fundamental transport processes in assemblies of silicon quantum dots" I. Balberg, E. Savir, J. Jedrzejewski, A. G. Nassiopoulou, S. Gardelis, Phys. Rev. B 75 235329 (2007)
- A.24** "Ultrafast transient photoinduced absorption in silicon nanocrystals: Coupling of oxygen-related states to quantized sublevels", E. Lioudakis, A. Othonos, A. G. Nassiopoulou, Appl. Phys. Lett. 90, 171103 2007 (Selected by the Virtual Journal of Nanoscale Science & Technology, 15 (2007) Issue 18)
- A.25** "Influence of grain size on ultrafast carrier dynamics in thin nanocrystalline silicon films", E. Lioudakisa, A. Othonos, A. G. Nassiopoulou, Ch. B. Lioutas and N. Frangis, Appl. Phys. Lett. 90, 191114 2007
- A.26** "Ultra-thin films with embedded Si nanocrystals fabricated by electrochemical dissolution of bulk crystalline Si in the transition regime between porosification and electropolishing", Gardelis, S., Tsiaoussis, I., Frangis, N., Nassiopoulou, A.G., Nanotechnology 18 (11), art. no. 115705 (2007)
- A.27** "The role of surface vibrations and quantum confinement effect to the optical properties of very thin nanocrystalline silicon films", Lioudakis, E., Antoniou, A., Othonos, A., Christofides, C., Nassiopoulou, A.G., Lioutas, Ch.B., Frangis, N., Journal of Applied Physics 102 (8), art. no. 083534 (2007)
- A.28** "Self-assembly of single thin Au nanoparticle chains on Si along V-groove-etched lines between micrometer-distant electrodes by dielectrophoresis" A. Zoy, A. A. Nassiopoulos and A. G. Nassiopoulou, Nanotechnology 18, 345608 (2007)
- A.29** "Ge quantum dot memory structure with laterally ordered highly dense arrays of Ge dots", A. G. Nassiopoulou, A. Olzierski, E. Tsoi, I. Berbezier and A. Karmous, J. Nanosci. Nanotechnol., vol. 7, 316-321 (2007)
- A.30** "Two-silicon-nanocrystal layer memory structure with improved retention characteristics", A. G. Nassiopoulou and A. Salonidou, J. Nanosci. Nanotechnol., vol. 7, 368-373 (2007)
- A.31** "A silicon thermal accelerometer without solid proof mass using porous silicon thermal isolation" D. Goustouridis, G. Kaltsas and A. G. Nassiopoulou IEEE Sensors Journal, vol. 7 No 7 983 (2007)
- A.32** "Quantum confinement and interface structure of Si nanocrystals of sizes 3-5 nm embedded in  $\alpha$ -SiO<sub>2</sub>" E. Lioudakis, A. Othonos, G. C. Hadjisavvas, P. C. Kelires and A. G. Nassiopoulou" Physica E 38 128-134 (2007)
- A.33** "Integrated inductors on porous silicon", H. Contopanagos, A. G. Nassiopoulou, Physica Status Solidi (A) 204 (5), pp. 1454-1458 (2007)
- A.34** "Novel microfluidic flow sensor based on a microchannel capped by porous silicon", D. N. Pagonis, A. Petropoulos, A., G. Kaltsas, A. G. Nassiopoulou, A. Tserepi, Physica Status Solidi (A) 204 (5), pp. 1474-1479 (2007)
- A.35** "Nanostructuring Si surface and Si/SiO<sub>2</sub> interface using porous-alumina-on-Si template technology. Electrical characterization of Si/SiO<sub>2</sub> interface" M. Kokonou and A. G. Nassiopoulou Physica E 38, 1-5 (2007)
- A.36** "Formation of confined macroporous silicon membranes on pre-defined areas on the Si substrate", D. N. Pagonis, A. G. Nassiopoulou, Physica Status Solidi (A) 204 (5), pp. 1335-1339 (2007)

- A.37** "Charging/discharging kinetics in LPCVD silicon nanocrystal MOS memory structures" V. Turchanikov, A. Nazarov, V. Lysenko, E. Tsoi, A. Salonidou and A. G. Nassiopoulou, *Physica E* 38 89-93 (2007)
- A.38** "Few nanometer thick anodic porous alumina films on silicon with high density of vertical pores", M. Kokonou, K. P. Giannakopoulos, A. G. Nassiopoulou, *Thin Solid Films* 515 (7-8), pp. 3602-3606 (2007)
- A.39** "A smart flow measurement system for flow evaluation with multiple signals in different operation modes", G. Kaltsas, P. Katsikogiannis, P. Asimakopoulos, A. G. Nassiopoulou, *Meas. Sci. Technol.* 18 (2007) 3617–3624
- A.40** "A novel microfabrication technology on organic substrates - Application to a thermal flow sensor", G. Kaltsas, A. Petropoulos, K. Tsougeni, D. N. Pagonis, T. Speliotis, E. Gogolides and A. G. Nassiopoulou, *Journal of Physics: Conference Series* 92 (2007) 012046
- A.41** "Ellipsometric analysis of ion-implanted polycrystalline silicon films before and after annealing", E. Lioudakis, A. G. Nassiopoulou and A. Othonos, *Thin Solid Films* 496 (2), pp. 253-258 (2006)
- A.42** "Femtosecond carrier dynamics in implanted and highly annealed polycrystalline silicon", E. Lioudakis, A. G. Nassiopoulou and A. Othonos, *Semiconductor Science and Technology* 21 (8), pp. 1041-1046 (2006)
- A.43** "Free-standing macroporous silicon membranes over a large cavity for filtering and lab-on-chip applications", D. N. Pagonis and A. G. Nassiopoulou, *Microelectronic Engin.* 83, 1421–1425 (2006)
- A.44** "Probing carrier dynamics in implanted and annealed polycrystalline silicon thin films using white light", E. Lioudakis, A. Othonos and A. G. Nassiopoulou, *Appl. Phys. Lett.* 88 (18) 181107 (2006)
- A.45** "Growth and characterization of high density stoichiometric SiO<sub>2</sub> dot arrays on Si through anodic porous alumina template", M. Kokonou, A. G. Nassiopoulou, K. P. Giannakopoulos, A. Travlos, T. Stoica, S. Kennou, *Nanotechnology* 17, 2146(2006)
- A.46** "Design and simulation of integrated inductors on porous silicon in CMOS-compatible processes", H. Contopanagos and A. G. Nassiopoulou, *Sol. St. Electronics*, vol. 50 (7-8) 1283 (2006)
- A.47** "Photoluminescence lifetimes of Si quantum dots", X. Zianni and A. G. Nassiopoulou, *J. Appl. Phys.* 100, 074312 (2006)
- A.48** "Thin porous anodic alumina films: Interface trap density determination", M. Theodoropoulou, P. K. Karahaliou, S. N. Georga, C. A. Krontiras, M. N. Pizanias, M. Kokonou and A. G. Nassiopoulou, *Ionics*, 11 (3-4), 236 (2005)
- A.49** "Ultra thin porous anodic alumina films with self-ordered cylindrical vertical pores on a p-type silicon substrate", M. Kokonou, A. G. Nassiopoulou and K. P. Giannakopoulos, *Nanotechnology* 16, 103, (2005)
- A.50** "Structural study of very thin anodic alumina films on silicon by anodization in citric acid aqueous solution", M. Kokonou, A. G. Nassiopoulou, K. G. Giannakopoulos, N. Boukos, A. Travlos, *J.Nanosc. and Nanotechnol.* v.5, 1-5, 454-458 (2005)
- A.51** "Electronic structure of C<sub>60</sub>, CuPc and C<sub>60</sub>/CuPc nanoparticles and their layers", *Fullerenes, Nanotubes and Carbon Nanostructures* 13(3), 259 (2005)

- A.52** “Fabrication and testing of an integrated thermal flow sensor employing thermal isolation by porous silicon membrane over air cavity”, D. N. Pagonis, G. Kaltsas, and A. G. Nassiopoulou, *J. Micromech. Microeng.* 14, 1-5, 793-797, (2004)
- A.53** “The influence of thermal treatment on the stress characteristics of suspended porous silicon membranes on silicon”, D. Papadimitriou, C. Tsamis, A. G. Nassiopoulou, *Sensors & Actuators (b)*, 103, 356-361, (2004)
- A.54** “Selective self-alignment of Au nanoparticle-coated K<sub>2</sub>SO<sub>4</sub> microcrystals in micrometer gratings of V-grooves on a silicon substrate”, A. G. Nassiopoulou, A. Zoy, V. Ioannou-Sougliridis, A. Olzierski, A. Travlos, J. L. Martinez-Albertos, B. Moore, *Nanotechnology* 15, 1-5, 352-356, (2004)
- A.55** “Growth of two-dimensional arrays of silicon nanocrystals in thin SiO<sub>2</sub> layers by low pressure chemical vapour deposition and high temperature annealing/oxidation. Investigation of their charging properties”, A. Salonidou, A. G. Nassiopoulou, A. Travlos, V. Ioannou-Sougliridis, E. Tsoi, *Nanotechnology* 15, 1-7, 1233-1239, (2004)
- A.56** “Transient and ac electrical transport under forward and reverse bias conditions in aluminium/ porous silicon/ p-cSi structures”, M. Theodoropoulou, P.K. Karahaliou, C. A. Krontiras, S. N. Georga, N. Xanthopoulos, C. Tsamis, A. G. Nassiopoulou, *J. Appl. Phys.* 96, 12, (2004)
- A.57** “Influence of magnetic field on electromagnetic instabilities in semiconductor superlattices”, R. H. Tarkhanyan and A. G. Nassiopoulou, *J. Nanosci. Nanotechnology* 4, 1085, (2004)
- A.58** “Two-dimensional arrays of nanometer scale holes and nano-V-grooves in oxidized Si wafers for the selective growth of Ge dots or Ge/Si hetero-nanocrystals”, A. Olzierski, A. G. Nassiopoulou, I. Raptis, T. Stoica, *Nanotechnology* 15, 1695-1700 (2004)
- A.59** “Transient and ac conductivity of nanocrystalline porous alumina thin films on silicon, with embedded silicon nanocrystals”, embedded silicon nanocrystals”, P. K. Karahaliou, M. Theodoropoulou, C. A. Krontiras, N. Xanthopoulos, S. N. Georga, and M. N. Pisanias M. Kokonou, A. G. Nassiopoulou, and A. Travlos *J. of Appl. Phys.*, 95,5, 2776-2780 (2004)
- A.60** “Gas flow meter for applications in medical equipment for respiratory control-Study of the package and housing”, G. Kaltsas and A. G. Nassiopoulou, *Sensors & Actuators A*, 100, 413-422, (2004)
- A.61** “Porous silicon membranes over cavity for efficient local thermal isolation on silicon for application in Si thermal sensors”, D. N. Pagonis, A. G. Nassiopoulou and G. Kaltsas, *J. Electrochem. Soc.* 151 (8) H 174-H179, (2004)
- A.62** R. H. Tarkhnyan and A. G. Nassiopoulou, *ibid*, 4 1085 (2004)
- A.63** “Temperature dependence of the transient and ac electrical conductivity of porous silicon thin films”, M. Theodoropoulou, C. A. Krontiras, N. Xanthopoulos, S. N. Georga, M. N. Pisanias, C. Tsamis and A. G. Nassiopoulou *Materials science and Engineering B*. v.101, (1-3), 334-337 (2003)
- A.64** “Thermal properties of suspended porous silicon micro-hotplates for sensor applications”, C. Tsamis, A. G. Nassiopoulou and A. Tserepi, *Sensors and Actuators B: Chemical*, 95(1-3), 78, (2003)
- A.65** “Calculated PL lifetimes of Si nanowires: The effect of a dispersion in the crystallographic orientations”, X. Zianni and A. G. Nassiopoulou, *Materials Science and Engineering B*, 101, 242, (2003)

- A.66** “Structural and photoluminescence properties of thin alumina films on silicon, fabricated by electrochemistry”, M. Kokonou, A. G. Nassiopoulou and A. Travlos, *Materials Science and Engineering B* 101 65, (2003)
- A.67** “Charging effects in silicon nanocrystals within SiO<sub>2</sub> layers, fabricated by chemical Vapor Deposition, oxidation, and annealing” D. N. Kouvatsos, V. Ioannou-Sougleridis and A. G. Nassiopoulou, *Appl. Phys. Lett.* 82(3) 397, (2003)
- A.68** “Influence of a high electric field on the photoluminescence from silicon nanocrystals in SiO<sub>2</sub>”, Ioannou-Sougleridis V., Kamenev B., Kouvatsos D.N., Nassiopoulou A.G. , *Materials Science and Engineering B-Solid State Materials for Advanced Technology*, 101 (1-3): 324-328 Aug. 15 2003
- A.69** “Charging effects in silicon nanocrystals embedded in SiO<sub>2</sub> films” D. N. Kouvatsos, V. Ioannou-Sougleridis and A. G. Nassiopoulou, *Mater. Scien. & Engineering B* 101, 270, (2003)
- A.70** “Fabrication of suspended thermally insulating membranes using front-side micromachining of the Si substrate: characterization of the etching process”, A. Tserepi, C. Tsamis, G. Kokkoris, E. Goggolides and A. G. Nassiopoulou, *J. of Micromech. & Microengin.* 13, 323, (2003)
- A.71** “Effect of high temperature annealing on the charge trapping characteristics of silicon nanocrystals embedded within SiO<sub>2</sub>”, V. Ioannou-Sougleridis, A. G. Nassiopoulou and A. Travlos, *Nanotechnology* 14, 1174, (2003)
- A.72** “Photoluminescence from SiO<sub>2</sub>/Si/SiO<sub>2</sub> structures”, P. Photopoulos, A. G. Nassiopoulou, *J. Phys.: Codens. Matter* 15, 3641 (2003)
- A.73** “Investigation of charging phenomena in silicon nanocrystal metal-oxide-semiconductor capacitors using ramp current-voltage measurements”, V. Ioannou-Sougleridis and A. G. Nassiopoulou, *J. Appl. Phys.* 94(6) 4084, (2003)
- A.74** “Self-assembling of Ge on finite Si (001) areas comparable with the island size”, L. Vescan, T. Stoica, B. Hollander, A. G. Nassiopoulou, A. Olzierski, I. Raptis, E. Sutter, *Appl. Phys. Lett.* 82(20) 3517, (2003)
- A.75** “Multi-component behavior of the photoluminescence lifetime in porous Si”, X. Zianni, A. G. Nassiopoulou, *Physica Status Solidi A-Applied research* 197 (2) 311-315, (2003)
- A.76** “Electromagnetic instability of surface waves in semiconductor superlattices”, R. H. Tarkhanyan, A. G. Nassiopoulou, *Journal of Nanoscience and Nanotechnology*, Vol. 3, (No 6), p. 549, (2003)
- A.77** “Fabrication of suspended porous silicon micro-hotplates for thermal sensor applications”, C. Tsamis, A. Tserepi, A. G. Nassiopoulou, *Phys. Stat. Sol. (a)*, 197 (2), 539, (2003)
- A.78** “Dry etching of Porous Silicon in High Density Plasmas”, A. Tserepi, C. Tsamis, E. Gogolides and A. G. Nassiopoulou, *Phys. Stat. Sol. (a)*, 197 (2), 163, (2003)
- A.79** “Transient and AC electrical conductivity of porous silicon thin films”, M. Theodoropoulou, C. A. Krontiras, N. Xanthopoulos, S. N. Georga, M. N. Pisanias, C. Tsamis and A. G. Nassiopoulou, *Phys. Stat. Sol. (a)*, 197 (2), 279, (2003)
- A.80** “Multi-component behavior of the photoluminescence lifetime in porous Si”, X. Zianni and A. G. Nassiopoulou, *Phys. Stat. Sol. (a)*, 197 (2), 311, (2003)

- A.81** “Implantation Masking Technology for Selective Porous Silicon Formation”, D. Pagonis, G. Kaltsas and A. G. Nassiopoulou, Phys. Stat. Sol. (a), 197 (2), 241, (2003)
- A.82** “Planar CMOS Compatible Process For The Fabrication of Buried Microchannels In Silicon, Using Porous Silicon Technology”, G. Kaltsas, D. N. Pagonis, A. G. Nassiopoulou, IEEE J. Microelectromech. Syst , 12 (6), (2003) pp. 863-872
- A.83** “Directional dependence of the spontaneous emission of Si quantum wires”, X. Zianni and A. G. Nassiopoulou, Phys. Rev. B, vol. 65 (35) 326 (2002)
- A.84** “Hydrogen catalytic reaction on Pd doped Porous Silicon”, C. Tsamis, L. Tsoura, A. Travlos, A. G. Nassiopoulou, C. E. Salmas, K. S. Hatzilyberis and G. P. Androustopoulos, IEEE Sensors Journal, Vol. 2 (2) 1530, (2002)
- A.85** “Structural and electrical quality of the high-k dielectric Y2O3 on Si (001): Dependence on growth parameters” A. Dimoulas, G. Velianitis, A. Travlos, V. Ioannou-Sougleridis and A. G. Nassiopoulou, Jour. of Appl. Phys., 92(2), (2002)
- A.86** “Characterization of a Silicon Thermal Gas-Flow Sensor With Porous Silicon Thermal Isolation”, G. Kaltsas, A. A. Nassiopoulos and A. G. Nassiopoulou, IEEE Sensors Journal, 2(5), 463-475, (2002)
- A.87** “Photoluminescence lifetimes in silicon quantum wires”, X. Zianni A. G. Nassiopoulou, Phys. Rev. B, vol. 66, 205 323, (2002)
- A.88** “GMR study leading to sensor fabrication on the Ag-Co system” M. Angelakeris, P. Pouloupoulos, O. Vallasiades, N. K. Flevaris, D. Niarchos and A. G. Nassiopoulou, Sensors and Actuators, A 91, 180-183, (2001)
- A.89** “Nonlinear electrical transport in NC-Si/CaF2 multilayer structures with ultrathin CaF2 layers”, V. Ioannou-Sougleridis, T. Ouisse, A. G. Nassiopoulou, F. Bassani and F. Arnaud d’ Avitaya, J. Appl. Phys. 89 (1), 610-614, (2001)
- A.90** “Electroluminescence from silicon nanocrystals in Si/CaF2 superlattices”, V. Ioannou-Sougleridis, A. G. Nassiopoulou, T. Ouisse, F. Bassani and F. Arnaud d’ Avitaya, Appl. Phys. Lett., 79(13) 2076, (2001)
- A.91** “Self-trapped excitons in silicon nanocrystals of sizes below 1.5 nm in Si/ SiO2 multilayers”, B. V. Kamenev and A. G. Nassiopoulou, Jour. of Appl. Phys., 90(11), 5735, (2001)
- A.92** “Dielectric Properties of nc-Si/CaF2 multiquantum wells”, V. Ioannou-Sougleridis, V. Tsakiri, A. G. Nassiopoulou, F. Bassani, S. Menard, F. Arnaud d’ Avitaya, Mater. Sci. and Engin. B69-70, 309-313, (2000)
- A.93** “Photo-and electroluminescence from nanocrystalline silicon single and multilayerstructures”, P. Photopoulos, A. G. Nassiopoulou, D. N. Kouvatsos and A. Travlos, Mater. Sci. & Eng. B69-70, 345-349, (2000)
- A.94** “Low temperature RAMAN and photoluminescence study of Si/CaF2 multiquantum wells”, D. Papadimitriou, A. G. Nassiopoulou, F. Bassani and F. Arnaud d’ Avitaya, Mat. Sci. & Engin. B69-70, 546-548, (2000)
- A.95** “Photoluminescence from nanocrystalline silicon in Si/SO2 superlattices”, P. Photopoulos, A. G. Nassiopoulou, D. N. Kouvatsos and A. Travlos, Appl. Phys. Lett, 76 (24), 3588-3590 (2000)
- A.96** “Trapping levels in nanocrystalline porous silicon”, M. L. Ciurea, M. Drăghici, S. Lazarnu, V. Iancu, A. Nassiopoulou, V. Ioannou and V. Tsakiri, Appl. Phys. Lett., 76 (21), p. 3067-3069, (2000)

- A.97** “Micro-Raman analysis of polysilicon membranes deposited on porous silicon channels” H. Taalat, S. Negm, H.E. Schaffer, G. Kaltsas, A. G. Nassiopoulou, *J. of Non-Crystalline Solids*, 266-269, 1345-1349 (2000)
- A.98** “Dependence of the radiative recombination lifetime upon electric field in silicon quantum dots embedded into SiO<sub>2</sub>”, T.Ouisse and A. G. Nassiopoulou, *Europhys. Lett*, 51 (2), pp. 168-173, (2000)
- A.99** “Room and low temperature voltage tunable electroluminescence from a single layer of silicon quantum dots sandwiched between two thin SiO<sub>2</sub> layers”, P. Photopoulos and A. G. Nassiopoulou, *Appl. Phys. Lett*, 77 (12), p. 1816-1818, (2000)
- A.100** “Porous silicon as an effective material for thermal isolation on bulk crystalline silicon”, A. G. Nassiopoulou and G. Kaltsas, *Phys. Stat. Sol. (a)* 182,307, (2000)
- A.101** “Oxidation-induced modifications of traps parameters in nanocrystalline porous silicon”, M. Draghici, M. Miu, A. Nassiopoulou, I. Kleps, A. Angelescu, M. L. Ciurea, *Phys. Stat. Sol. (a)* 182,239 (2000)
- A.102** “Electrical modeling of Si/SiO<sub>2</sub> superlattices”, T.Ouisse, V. Ioannou-Sougleridis, D. Kouvatso and A. G. Nassiopoulou, *J. Phys. D: Appl. Phys.* 33, 2691-2698, (2000)
- A.103** “Micro-Raman analysis of polysilicon membranes deposited on porous silicon channels”, H. Talaat, S. Negm, H. E. Schaffer, G. Kaltsas and A. G. Nassiopoulou, *J. of Non-Cryst. Solids*, 266-269, 1345-1349, (2000)
- A.104** “Novel C-MOS compatible monolithic silicon gas flow sensor with porous silicon thermal isolation”, G. Kaltsas and A. G. Nassiopoulou, *Sens. & Actuators A*, 76(1-3) p.133, (1999)
- A.105** “Giant magnetoresistance Co/Cu multilayer sensors for use in magnetic field mapping”, Christides C., Stavroyiannis S., Kallias G., Nassiopoulou A.G., Niarchos D., *Sensors and Actuators A-Physical* 76 (1-3): 167-171 Aug. 30 1999
- A.106** “Electroluminescence from Si/CaF<sub>2</sub> multilayers grown by molecular beam epitaxy” V. Ioannou-Sougleridis, V. Tsakiri, A. G. Nassiopoulou, P. Photopoulos, F. Bassani and F. Arnaud d’ Avitaya *Phys. St. Sol (a)* 165, 97, (1998)
- A.107** “Stable visible photo- and electroluminescence from nanocrystalline silicon thin films fabricated on thin SiO<sub>2</sub> layers by low pressure chemical vapour deposition”, A. G. Nassiopoulou, V. Ioannou-Sougleridis, P. Photopoulos, A. Travlos, V. Tsakiri and D. Papadimitriou, *Phys. St. Sol. (a)* 165,79, (1998)
- A.108** “Polarized Raman and Photoluminescence study on silicon quantum wires”, D.Papadimitriou and A.G. Nassiopoulou, *J.Appl.Phys.* 84(2), 1059-1063, (1998)
- A.109** “Porous silicon of variable porosity under high hydrostatic pressure: Raman and Photoluminescence studies”, D. Papadimitriou, Y. S. Raptis, A. G. Nassiopoulou and G. Kaltsas, *Phys. St. Sol. (a)* 165 (1), 43, (1998)
- A.110** “Light emitting structures based on nanocrystalline (Si/CaF<sub>2</sub>) multiquantum wells”, A. G. Nassiopoulou, V. Tsakiri, V. Ioannou-Sougleridis, P. Photopoulos, S. Menard, F. Bassani and F. Arnaud d’ Avitaya, *J. of Luminescence*, 22, 2313, (1998)



- A.111** “Stress effect on suspended polycrystalline silicon membranes fabricated by micromachining of porous silicon”, G. Kaltsas, A. G. Nassiopoulou, M. Siakavellas and E. Anastassakis, *Sensors and Actuators A68*, 429-434 (1998)
- A.112** “Micro-Raman characterization of stress distribution within free standing mono- and polycrystalline silicon membranes”, S. Siakavellas, E. Anastassakis, G. Kaltsas and A. G. Nassiopoulou, *Microel. Engineer.* 41/42, 469-472, (1998)
- A.113** “Raman microprobe analysis of strained polysilicon deposited layers”, H. Talaat, S. Negm, H. E. Schaffer, F. Adar, A. G. Nassiopoulou, *Appl. Surf. Sci* 123/124, 742-745, (1998)
- A.114** “High crystalline quality titanium disilicides formed by sputter deposition of Ti/Si multilayers and annealing”, P. Revva, A. Kastanas, A. Travlos and A. G. Nassiopoulou, *Vacuum*, 51(3), 355-337, (1998)
- A.115** “Thickness determination of thin films based on X-ray signal decay law”, G. Kaltsas, N. Glezos, E. Valamontes and A. G. Nassiopoulou *Surf. and Inter. Analysis* 26 , 876, (1998)
- A.116** “High Resolution Electron Microscopy Study of New Erbium Silicide Superstructures, based on the ThSi<sub>2</sub> Structure”, N. Frangis, G. Van Tendeloo, J. Van Landuyt, G. Kaltsas, A. Travlos, A. G. Nassiopoulos, *J. of Crystal Growth*, 172, 175-182, (1997)
- A.117** “Low Specific Contact Resistivity Titanium Silicides on n+ and p+ silicon by Sputtering Deposition of Ti/Si multilayers and annealing”, P. Revva, A. Castanas and A. G. Nassiopoulos, *J. Electroch. Society*, vol. 144(11), 4072, (1997)
- A.118** “Bulk silicon micromachining using porous silicon sacrificial layers”, G. Kaltsas and A. G. Nassiopoulos, *Microelectronic Engineering*, 35, 397, (1997)
- A.119** “Highly Anisotropic Silicon Reactive Ion Etching for Nanofabrication Using Mixtures of SF<sub>6</sub> and CHF<sub>3</sub> gases”, S. Grigoropoulos, E. Gogolides and A. G. Nassiopoulos, *J. Vacuum Science and Technol. B* 15(3) 640, (1997)
- A.120** “Electroluminescent Solid State Devices based on Silicon Nanowires, fabricated by using lithography and etching techniques”, A. G. Nassiopoulou, S. Grigoropoulos and D. Papadimitriou, *Thin Solid Films*, 297, 176, (1997)
- A.121** “Front-side bulk silicon micromachining using porous silicon technology”, G. Kaltsas and A. G. Nassiopoulos, *Sensors and Actuators A*, A65, 175-179, (1998)
- A.122** “High pressure studies on the origin of porous silicon photoluminescence”, D. Papadimitriou, Y. S. Raptis and A. G. Nassiopoulou, *Physical Rev. B*, 58(21), 14089, (1998)
- A.123** “Growth of erbium-silicide films on (100) silicon as characterized by electron microscopy and diffraction”, N. Frangis, J. Vandanduyt, G. Kaltsas, A. G. Nassiopoulos, *J. of Crystal Growth* 172(1-2): 175-182, (1997)
- A.124** “Characterization of light emitting silicon nanopillars produced by lithography and etching”, S. Grigoropoulos, A. G. Nassiopoulos, A. Travlos, D. Papadimitriou, S. Kennou and S. Ladas, *Appl. Surf. Sci.*, 102, 377, (1996)
- A.125** “Electroluminescent device based on silicon nanopillars”, A. G. Nassiopoulos, S. Grigoropoulos and D. Papadimitriou, *Appl. Phys. Letters*, 69(15), 2267, (1996)

- A.126** “New Erbium Silicide Superstructures: A study by High Resolution Electron Microscopy”, N. Frangis, G. Van Landuyt, G. Kaltsas, A. Travlos, A. G. Nassiopoulou, *Phys. Stat. Solidi*, (a) 158 p. 107-116, (1996)
- A.127** “Comparison of Scanning X-ray Microfluorescence and Energy Dispersive X-ray Analysis for the Elemental Characterization of Thin Coatings”, E. Valamontes and A. G. Nassiopoulos, *Microchimica Acta*, 13, 597-603, (1996)
- A.128** “Electron Probe X-ray Analysis of Coatings. Sensitivity and Resolution”, E. Valamontes and A. G. Nassiopoulos, *Microchimica Acta*, 13, 605-610, (1996)
- A.129** “Application of the Boltzmann transport equation to the thickness determination of thin films”, G. Kaltsas, N. Glezos, E. Valamontes, A. G. Nassiopoulos, *Microchimica Acta [Suppl.]* 13, 349, (1996)
- A.130** “Erbium silicide films on (100) silicon, grown in high vacuum: fabrication and properties”, G. Kaltsas, A. Travlos, P. Revva, A. G. Nassiopoulos, A. Traverse, *Thin Solid Films*, 275, 87, (1996)
- A.131** “High Crystalline Quality Erbium Silicide Films on (100) Silicon, Grown in High Vacuum”, G. Kaltsas, A. G. Nassiopoulos, A. Travlos, N. Frangis, J. Van Landuyt, *Appl. Surf. Science*, Vol. 102, 151, (1996)
- A.132** “Electron Microscopy Characterization of High Crystalline Quality Erbium Silicide Films on (100) Silicon, Grown in High Vacuum”, N. Frangis, G. Van Landuyt, G. Kaltsas, A. Travlos, A. G. Nassiopoulos, *Phys. Stat. Solidi*, (a) 158, (1996)
- A.133** “Sub-micrometer luminescent porous silicon structures using lithographically patterned substrates”, A. G. Nassiopoulos, S. Grigoropoulos, L. T. Canham, A. Halimaoui, I. Berbezier, E. Gogolides and D. Papadimitriou, *Thin Solid Films*, 255(2), 329, (1995)
- A.134** “Visible luminescence from one and two-dimensional silicon structures produced by conventional lithographic and reactive ion etching techniques”, A. G. Nassiopoulos, S. Grigoropoulos, D. Papadimitriou and E. Gogolides, *Appl. Phys. Letters*, 66(9), 1114, (1995)
- A.135** “Highly anisotropic room temperature sub-half-micron silicon Reactive Ion Etching using fluorine-only containing gases”, E. Gogolides, S. Grigoropoulos and A. G. Nassiopoulos, *Microelectronic Engineering*, 27, 449, (1995)
- A.136** “Light emission from silicon nanostructures, produced by optical lithography and etching”, A. G. Nassiopoulos, S. Grigoropoulos, D. Papadimitriou and E. Gogolides, *Physica Status Solidi*, (b) 190, 91, (1995)
- A.137** “Room and low temperature electrical measurements for the interface characterization of Titanium disilicides on Silicon from multilayer Titanium/Silicon structures”, P. Revva, A. G. Nassiopoulos and A. Travlos, *J. de Phys. IV*, C6, vol. 4, C6-93, (1994)
- A.138** “Characterization of TiSi<sub>2</sub>/Si interface in Titanium disilicide films, formed by deposition of alternate Ti/Si layers and annealing”, P. Revva, A. G. Nassiopoulos and A. Travlos, *J. Appl. Phys.*, 75(9), 4533, (1994)
- A.139** “Titanium disilicide on Si by interdiffusion of Ti and  $\alpha$ -Si multilayers: Transmission Electron Microscopy, Spectroscopic Ellipsometry and resistivity measurements”, A. G. Nassiopoulos, D. Tambouris, N. Frangis, S. Logothetides, S. Georga, Ch. Krontiras and N. Xanthopoulos, *Thin Sol. Films*, 247, 44, (1994)
- A.140** “Further characterization of the positive tone wet silylation process with the AZ 5214 TM photoresist”, E. Gogolides, K. Yannakopoulou, A. Traverse, A. G. Nassiopoulos, E. Tsoi and M. Hatzakis, *Microelectronic Engineering*, 25, 75, (1994)

- A.141** “Characterization of a positive tone wet silylation process with the AZ5214 TM photoresist”, E. Gogolides, K. Yannakopoulou, A. G. Nassiopoulou, E. Tsoi and M. Hatzakis, *Microelectronic Engineering*, 21, 263-66, (1993)
- A.142** “Monte-Carlo simulations of the point-to-point resolution in Scanning Auger Microscopy and X-ray Microanalysis of thin overlayers”, E. Valamontes, A. G. Nassiopoulou and N. Glezos, *Surf. Interf. Analysis*, 19, 419, (1992)
- A.143** “Wet silylation and dry development with the AZ 5214TM photoresist”, E. Gogolides, E. Tsoi, A. G. Nassiopoulou and M. Hatzakis, *J. Vac. Sci. Technol. B* 10(6), 2610, (1992)
- A.144** “Titanium disilicide formation by interdiffusion of Ti/ $\alpha$ -Si multilayers for VLSI applications. Influence of the bilayer Si/Ti thickness ratio on the film properties”, A. G. Nassiopoulou, D. Tambouris, A. Traverse, A. Travlos, A. Traverse, P. Aloupogiannis, *J. Appl. Phys.*, 72(10), 4660, (1992)
- A.145** “Lateral Resolution of Auger Electron Spectroscopy in the energy range 5-100keV. Thin overlayers on a high-Z material substrate”, N. Glezos and A. G. Nassiopoulou, *Surf. Science*, 254, 309-319, (1991)
- A.146** “Backscattering and X-ray induced correction factors for AES of thin overlayers”, E. Valamontes, A. G. Nassiopoulou, N. Glezos, *Surf. Interf. Anal.*, 16, 203, (1990)
- A.147** “Monte-Carlo calculations of the X-ray induced enhancement signal in EPMA and AES of thin films on a bulk material”, A. G. Nassiopoulou, E. Valamontes, *Surf. Interf. Anal.*, 15, 405, (1990)
- A.148** “Anomalous effects on the current - voltage characteristics of p-channel Metal -oxide semiconductor transistors in the temperature range 4.2 K - 50 K.”, A. G. Nassiopoulou, D. Tsamakis, E. Rocofyllou, *J. Appl. Phys.* 68(4), 1896, (1990)
- A.149** “Electronic Core Level Microanalyses and Microscopies in a Polyvalent Apparatus”, J. Cazaux, D. Gramari, O. Jbara, D. Mouze, A. G. Nassiopoulou, and X. Thomas, *Jour. Electr. Micr. Techn.*, Vol. 11, No 3, 222, (1989)
- A.150** “Anomalous behavior of the static current-voltage characteristics of n-channel MOSFETs in the temperature range 4.2K-14K”, E. Rocofyllou, A. G. Nassiopoulou, D. Tsamakis, F. Balestra, *Sol. Stat. Electr.*, 32(8), 603 (1989)
- A.151** “SEELS in the Reflection mode, compared to EELS of fast electrons”, A. G. Nassiopoulou, J. Cazaux *Surface Science* 165, 203-220, (1986)
- A.152** “Slow-Electron-Energy-Loss Spectroscopy for Surface Microanalysis”, A. G. Nassiopoulou, J. Cazaux, *Surface Science* 149, 313-325(1985)
- A.153** “Slow-Electron-Energy-Loss Spectra and non-dipole transitions in Nickel”, J. Cazaux, A. G. Nassiopoulou, *Surface Science* 162, 965-970, (1985)
- A.154** “The effects of X-ray induced Auger electrons in Auger Microanalysis”, J. Cazaux, D. Gramari, S. Moutou, A. G. Nassiopoulou, *Journ. Phys.*, 45, C2-337-41, (1984)
- A.155** “X-ray Photoelectron Microprobe analysis and related techniques”, J. Cazaux, D. Gramari, D. Mouze, A. G. Nassiopoulou, J. Perrin, *Journ. Phys.*, 45, C2 - 271-75, (1984)
- A.156** “Continuous X-ray induced Auger Microprobe Analysis and Microscopy: first results”, A. G. Nassiopoulou, D. Gramari, J. Cazaux, *Surface Science*, 129, 247-264, (1983)

- A.157** “Confinement d'ions dans une cage cylindrique a champ quadrupolaire HF. Application a la spectrometrie de masse. I. Partie Theorique”, A. G. Nassiopoulou, P.A. Moller, A. Septier, Rev. Phys. Appliquee, 15, 1529-41, (1980)
- A.158** “Confinement d'ions dans une cage cylindrique a champ quadrupolaire HF, Application a la spectrometrie de masse. II. Partie Experimentale”, A. G. Nassiopoulou, P. A. Moller, A. Septier, Rev. Phys. Appliquee, 15, 1543-51, (1980)

## **B. Chapters in Books**

- B.1** "Optical properties of Si quantum wires and dots", X. Zianni and A. G. Nassiopoulou, Handbook of Theoretical and Computational Nanotechnology, edited by Michael Rieth and Wolfram Schommers, American Scientific Publishers, vol. 1 chapter 94, pages 1-37, (2005)
- B.2** “Silicon nanocrystals in SiO<sub>2</sub> thin layers”, A. G. Nassiopoulou, Encyclopedia of Nanoscience and Nanotechnology, edited by H. S. Nalwa (American Scientific Publishers, California, 2004), vol. 9 p. 793-813, (2004)
- B.3** “Local formation and patterning of porous silicon”, A. G. Nassiopoulou, paper in: “Properties of Porous Silicon” by L. T. Canham, EMIS Datareviews Series, UK (1997)

## **C. Publications in Conference Proceedings**

### **C1. International Conference Proceedings**

- C1.1** “Determination of critical points on silicon nanofilms: surface and quantum confinement effects”, Emmanouil Lioudakis, Andreas Othonos, A. G. Nassiopoulou, Physica status solidi (c), Volume 5, Issue 12, December 2008, pp. 3776-3779
- C1.2** “Dielectric characterization of macroporous thick silicon films in the frequency range 1 Hz-1 MHz”, M. Theodoropoulou, D. N. Pagonis, A. G. Nassiopoulou, C. A. Krontiras, S. N. Georga, Physica status solidi (c), Volume 5, Issue 12, December 2008, pp. 3597-3600
- C1.3** “Porous anodic alumina thin films on Si: interface characterization”, V. Gianneta, A. G. Nassiopoulou, C. A. Krontiras, S. N. Georga, Physica status solidi (c), Volume 5, Issue 12, December 2008, pp. 3686-3689
- C1.4** “Evaluation of a gas flow sensor implemented on organic substrate”, A. Petropoulos, G. Kaltsas, T. Speliotis, A.G. Nassiopoulou, Physica status solidi (c), Volume 5, Issue 12, December 2008, pp.3839-3842

- C1.5** “On-chip RF-shielding by mesoporous Si microplate measured through an integrated coplanar waveguide”, H. Contopanagos, F. Zacharatos and A. G. Nassiopoulou, Materials of the 6th International Conf. on Porous Semiconductors – Science and Technology, Mallorca, Spain, pp. 80-81 (10-14 March 2008).
- C1.6** “Calculations of the optical response of metalodielectric nanostructures of nonspherical particles by a layer-multiple scattering method”, N. Papanikolaou, G. Gantzounis, and N. Stefanou, Proc. of SPIE, 6988 69881D(1-12) (2008), SPIE, Photonics Europe, Strasbourg, April (2008)
- C1.7** "Spectroscopic characterization of thin anodic silicon layers grown by short monopulses of current", S. Gardelis, S. Jaziri, A. G. Nassiopoulou, A.G., AIP Conference Proceedings 935, pp. 87-91 (2007)
- C1.8** "Nanostructuring SiO<sub>2</sub>/Si(100) surface for lateral ordering of self-assembled semiconductor quantum dots" (invited) A. G. Nassiopoulou and M. Kokonou, Physics, Chemistry and Applications of Nanostructures, World Scientific Publishing, Edited by V E Borisenko, S V Gaponenko and V S Gurin p. 407 (2007)
- C1.9** "Structural and light-emitting properties of ultra thin anodic silicon films formed at the early stages of bulk silicon anodization" (invited) S. Gardelis, A. G. Nassiopoulou, I. Tsiaoussis and N. Frangis, Physics, Chemistry and Applications of Nanostructures, World Scientific Publishing, Edited by V E Borisenko, S V Gaponenko and V S Gurin p. 407 (2007)
- C1.10** “Porous silicon for sensors and on-chip integration of RF components”, A. G. Nassiopoulou (invited paper), Proceedings of the 4th International Conference on Microelectronics, Devices and Materials, Slovenia 13-15 September 2006, p. 33
- C1.11** “Integrated inductors on porous silicon”, H. Contopanagos, A. G. Nassiopoulou, Proceedings of the 5th International Conference on Porous Semiconductors-Science and Technology (PSST), Sitges-Barcelona, 12-17 March 2006, p. 124
- C1.12** “A silicon integrated thermal liquid flow sensor on porous silicon micro-hotplate”, D. N. Pagonis, G. Kaltsas and A. G. Nassiopoulou, Proceedings of the 20th Eurosensors Conference, Göteborg, Sweden, 17-20 September 2006
- C1.13** “Local formation of suspended macroporous Si layers on a Si substrate”, D.N. Pagonis, A. G. Nassiopoulou, Proceedings of the 5th International Conference on Porous Semiconductors-Science and Technology (PSST), Sitges-Barcelona, 12-17 March 2006, p. 276
- C1.14** “Novel microfluidic flow sensor fabricated using porous silicon technology”, D.N. Pagonis, A. Petropoulos, G. Kaltsas, A.G. Nassiopoulou, A. Tserepi, Proceedings of the 5th International Conference on Porous Semiconductors-Science and Technology (PSST), Sitges-Barcelona, 12-17 March 2006, p. 296
- C1.15** "Generation of guided terahertz electromagnetic waves in semiconductor superlattices", R H Tarkhanyan and A. G. Nassiopoulou, J. Phys.: Conf. Ser. 10 19-22 (2005)
- C1.16** "Silicon nanocrystal memories by LPCVD of amorphous silicon, followed by solid phase crystallization and thermal oxidation", E Tsoi, P Normand, A G Nassiopoulou, V Ioannou-Sougleridis, A Salonidou and K Giannakopoulos, J. Phys.: Conf. Ser. 10 31-34 (2005)
- C1.17** “Charging characteristics of Si nanocrystals embedded within SiO<sub>2</sub> in the presence of near-interface oxide traps”, V Ioannou-Sougleridis and A. G. Nassiopoulou, J. Phys.: Conf. Ser. 10 39-42 (2005)

- C1.18** “Two-dimensional arrays of ordered, highly dense and ultra-small Ge nanocrystals on thin SiO<sub>2</sub> layers”, I Berbezier, A Karmous, A Ronda, T Stoica, L Vescan, R Geurt, A Olzierski, E Tsoi and A. G. Nassiopoulou, *J. Phys.: Conf. Ser.* 10 73-76 (2005)
- C1.19** “Electrical conductivity of Au-nanoparticle-coated K<sub>2</sub>SO<sub>4</sub> microcrystals deposited by DC trapping”, A Zoy, A G Nassiopoulou, V Ioannou-Sougliridis, M Murugesan and B D Moore, *J. Phys.: Conf. Ser.* 10 105-108 (2005)
- C1.20** “Nanotemplate alumina films on a silicon substrate fabricated by electrochemistry”, M Kokonou, A G Nassiopoulou, K P Giannakopoulos and N Boukos, *J. Phys.: Conf. Ser.* 10 159-162 (2005)
- C1.21** “Interface traps density of anodic porous alumina films of different thicknesses on Si”, M Theodoropoulou, P K Karahaliou, S N Georga, C A Krontiras, M N Pisanias, M Kokonou and A G Nassiopoulou, *J. Phys.: Conf. Ser.* 10 222-225 (2005)
- C1.22** “Ultrafast carrier dynamics in highly implanted and annealed polycrystalline silicon films”, E Lioudakis, A G Nassiopoulou and A Othonos, *J. Phys.: Conf. Ser.* 10 263-266 (2005)
- C1.23** “Combination of integrated thermal flow and capacitive pressure sensors for high sensitivity flow measurements in both laminar and turbulent regions”, G Kaltsas, D Goustouridis, A G Nassiopoulou and D Tsoukalas, *J. Phys.: Conf. Ser.* 10 277-280 (2005)
- C1.24** “A microcontroller-based interface circuit for data acquisition and control of a micromechanical thermal flow sensor”, P Asimakopoulos, G Kaltsas and A G Nassiopoulou, *J. Phys.: Conf. Ser.* 10 301-304 (2005)
- C1.25** “Stress characteristics of suspended porous silicon microstructures on silicon”, K Anestou, D Papadimitriou, C Tsamis and A G Nassiopoulou, *J. Phys.: Conf. Ser.* 10 309-312 (2005)
- C1.26** "Porous Si for sensor applications", A. G. Nassiopoulou (invited paper) in "Nanostructured and Advanced Materials", edited by: A. Vaseashta, D. Dimova-Malinovska and J. M. Marshal, NATO Science Series II. Mathematics, Physics and Chemistry, vol. 204, pages 189-204, (2005)
- C1.27** "Optical emission behavior of Si quantum dots" X. Zianni and A. G. Nassiopoulou (invited paper), in "Quantum dots: Fundamentals, Applications and Frontiers" edited by: B. A. Joyce et al., NATO Science Series II., Mathematics, Physics and Chemistry, vol. 190, pages 369-376 (2005)
- C1.28** “Semiconductor nanocrystals in thin SiO<sub>2</sub> layers for non-volatile memories”, A. G. Nassiopoulou, A. Salonidou, A. Olzierski, M. Kokonou, E. Tsoi, P. Normand, K. Giannakopoulos, Proceedings of the International workshop on semiconductor nanocrystals (SEMINANO) held in Budapest, September 10-12, 2005, p.p. 405-410 (2005)
- C1.29** “The influence of thermal treatment on the stress characteristics of suspended Porous Silicon membranes on silicon”, D. Papadimitriou, C. Tsamis and A. G. Nassiopoulou, Eurosensors XVII, Guimaraes, Portugal, (September 21 - 24, 2003), Published in the Proceedings
- C1.30** “Porous Silicon for chemical sensors”, NATO ARW Summer School, Frontiers in Molecular-scale Science and Technology of nanocarbon, nanosilicon and biopolymer integrated nanosystems”, C. Tsamis and A. G. Nassiopoulou, Ilmenau, Germany, Published in the Proceedings
- C1.31** “Flow study in both turbulent and laminar flow with a system of thermal flow and capacitive pressure sensors”, G. Kaltsas, D. Goustouridis, A. G. Nassiopoulou, D. Tsoukalas, S. Chantzandroulis, “EUROSENSORS XVII, Guimaraes Portugal, (September 21-24, 2003), Published in the Proceedings, p.22

- C1.32** “Interband transitions in Si Nanostructures within effective mass approximation”, X. Zianni, A. G. Nassiopoulou, (Invited talk), Nanomeeting 2003, Minsk, Belarus (May, 2003), published in the proceedings
- C1.33** “Silicon nanocrystals in SiO<sub>2</sub> for memory devices”, A.G. Nassiopoulou, V. Ioannou-Sougleridis, A. Travlos (invited paper) NATO ARW, “Frontiers in molecular-scale science and technology of nanocarbon, nanosilicon and biopolymer integrated nanosystems” Illmenau, Germany (July 12-16 2003). Published in the proceeding p.45 (2003)
- C1.34** “A novel method for the fabrication of suspended porous silicon membranes for chemical sensors”, C. Tsamis, A. Tserepi and A.G. Nassiopoulou, Proceedings of the International Meeting on Chemical Sensors, Boston, 7-10 July 2002, USA
- C1.35** “Thermal properties of suspended porous silicon micro-hotplates for thermal sensor applications”, C. Tsamis, A. Tserepi and A. G. Nassiopoulou, Proceedings of Eurosensors XVI, Prague, Czech Republic, September 15-18, 2002
- C1.36** “Gas Flow Meter for Applications in Medical Equipment for Respiratory Control - Study of the Package and Housing”, G. Kaltsas and A. G. Nassiopoulou, Proceedings of Eurosensors XVI - 16th European Conference on Solid-State Transducers, Prague, Czech Republic, Sept. 15-18, 2002
- C1.37** “Fabrication of suspended membranes for thermal sensors using high-density plasma etching” A. Tserepi, C. Tsamis and A. G. Nassiopoulou, Proceedings of the Symposium on “Design, Test, Integration and packaging of MEMS/MOEMS”, DTIP 2002, Cannes-Mandelieu, France
- C1.38** “Carrier transport and electroluminescence in Si/CaF<sub>2</sub> superlattices” (invited paper), V. Ioannou-Sougleridis, A. G. Nassiopoulou, T. Ouisse, F. Bassani and F. Arnaud d’ Avitaya, in: Physics, Chemistry and Applications of Nanostructures 2001, Proceed. of Nanomeeting 2001, ed. by: V. E. Borisenko, S. V. Gaponenko and V. S. Gurin, World Scientific, p. 433, 2001
- C1.39** “Porous silicon as an effective material for thermal isolation on bulk crystalline silicon”, A. G. Nassiopoulou and G. Kaltsas, Proceed. of the 2nd Intern. Conf. on Porous Semiconductors Science and Technology, p.79, 2000
- C1.40** “Oxidation-induced modifications of trap’s parameters in nanocrystalline porous silicon”, M. Draghici, M. Miu, A. G. Nassiopoulou, I. Kleps, A. Angelescu, M. L. Ciurea, Proceed. of the 2nd Intern. Conf. on Porous Semiconductors Science and Technology, p. 286-287, Madrid, 12-17 March 2000
- C1.41** “Investigation of electron and photon properties of highly porous silicon under externally controlled uniaxial strain” D. Papadimitriou, A. G. Nassiopoulou, E. Liarokapis and V. Tsakiri, Proceed. of the 2nd Intern. Conf. on Porous Semiconductors Science and Technology, p.196, Madrid, 12-17 March 2000
- C1.42** “Silicon nanostructures in Si/SiO<sub>2</sub> superlattices for light emission applications: possibilities and limits”, A. G. Nassiopoulou, T. Ouisse and P. Photopoulos, in: Frontiers of Nano-Optoelectronic System, NATO ASI Series, Kuwer academic publishers, edited by: L. Pavesi and E. Buzaneva, pp.137-146 (2000)
- C1.43** “Low dimensional silicon for integrated optoelectronics”, A. G. Nassiopoulou, (invited paper), CAS’98, Proceedings, vol.2 p. 417 (1999)

- C1.44** “Nanocrystalline silicon for light emitting device applications” (invited paper), A.G. Nassiopoulou, P. Photopoulos and A. Travlos, in: “Physics Chemistry and Applications of Nanostructures”, 1999, Edited by: V. E. Borisenko, A. B. Filonov, S. V. Gaponenko, V. S. Gurin, World Scientific p. 356 (1999)
- C1.45** “Microraman study of mechanical stress in polycrystalline silicon bridges”, H. Talaat, S. Negm, H. Schaffer, G. Kaltsas and A. G. Nassiopoulou, Proceed. MRS vol. 505, p. 495 (1998)
- C1.46** “Electroluminescent devices based on zero- and one-dimensional silicon structures”, A. G. Nassiopoulos, V. Ioannou Souglerides, S. Grigoropoulos and D. Papadimitriou, Mat. Res. Soc. Symp. Proc. Vol. 459, 663, (1997)
- C1.47** “Application of Porous Silicon to Silicon Micromachining”, G. Kaltsas and A. G. Nassiopoulos, Mat. Res. Soc. Symp. Proc. Vol. 459 249, (1997)
- C1.48** “Recent progress in light emitting Si/CaF<sub>2</sub> multiquantum wells”, F. Arnaud D’Avitaya, F. Bassani, I. Mihalescu, A. G. Nassiopoulou (invited paper), “Physics, Chemistry and Applications of Nanostructures”, edited by V.E. Borisenko A. B. Filonov, S. V. Gaponenko and V. S. Gurin, p. 3, (1997)
- C1.49** “Light Emitting Properties of Silicon Nanopillars produced by lithography and etching” A. G. Nassiopoulos, S. Grigoropoulos and D. Papadimitriou, (Invited paper), Electrochemical Society Proceedings, 95-25, (1996), 296
- C1.50** “Silicon nanostructures: a way for Si Optoelectronics?”, F. Arnaud d'Avitaya, F. Bassani, L. Vervoort, A. G. Nassiopoulos, S. Grigoropoulos, E. Gogolides, I. Mihalescu, J. C. Vial, S. Ossicini, A. Fasolino and F. Bernardini (invited paper) Proc. International Conference Nanomeeting-95, Minsk, Belarus, May 15-19, (1995)
- C1.51** “Luminescence from silicon nanostructures fabricated by using conventional lithographic and Reactive Ion Etching techniques”, A. G. Nassiopoulos, S. Grigoropoulos, A. Travlos, S. Ladas, S. Kennou, I. Raptis and D. Papadimitriou, Proceed. of the 187th Meeting of the Electroch. Soc., Electrochemical Society Proceed, Vol. 95-8, p. 27, (1995)
- C1.52** “Highly anisotropic silicon Reactive Ion Etching for nanofabrication with fluorine only containing gases”, S. Grigoropoulos, E. Gogolides and A. G. Nassiopoulos, ULSI Science and Technology 95, 187th Meeting of the Electrochem. Soc., Electrochemical Soc. Proceedings, Vol. 95(5), p.275, (1995)
- C1.53** “TiSi<sub>2</sub>/Si interface of silicide formed by annealing of multilayer Ti/Si structures on silicon”, A. G. Nassiopoulou, N. Frangis, A. Travlos and P. Revva, Inst. Phys. Conf. Ser. No 134 Section 4, (1993)
- C1.54** “Point-to-point resolution in Scanning Auger Electron Spectroscopy at high primary beam energies for Surface and Interface Analysis”, A. G. Nassiopoulos and N. M. Glezos in: Equilibrium Structure and Properties of surfaces and Interfaces, edit: A. Gonis and G. M. Stocks, NATO ASI ser. B, 300 (1992) 329
- C1.55** “La Microanalyse X par Microsonde Electronique”, A. G. Nassiopoulos, Review article, Volume edited for a COMETT project/volet C, (1992)
- C1.56** “Surface and interface roughness of thin titanium silicides grown on silicon by interdiffusion of Ti and  $\alpha$ -Si thin films”, A. G. Nassiopoulos, D. Tambouris and A. Travlos, Electron Microscopy, vol. 2, EUREM 92, p. 729



- C1.57** “Characterization of a positive-tone wet silylation process with the AZ5214 TM photoresist”, E. Gogolides, K. Yannakopoulou, A. G. Nassiopoulou, E. Tsoi and M. Hatzakis, Proceed. 36th Intern. Cong. on Electr. Ion and Photon Beams (EIPB) (1992)
- C1.58** “Application of electron transport equations in X-ray Microanalysis of thin overlayers and in film thickness measurements”, N. Glezos, A. G. Nassiopoulou, E. Valamontes, Proc. VII Nat. Congress on Sol. State Physics, (1991) 16
- C1.59** “Lateral resolution in X-ray Microanalysis of thin over-layers and thin unsupported films”, A. G. Nassiopoulou and E. Valamontes. Proc. VII Nat. Congress on Sol. State Phys., (1991) 497
- C1.60** “Interaction of  $\alpha$ -Si/Ti multilayers for TiSi<sub>2</sub> formation, Application to shallow junctions for submicron circuits”, A. G. Nassiopoulou, D. Tambouris, T. Travlos, P. Aloupogiannis, A. Traverse, E. Tsoi, Proc. VII Nat. Congress on Sol. St. Phys., (1991) 150
- C1.61** “High Spatial Resolution in Scanning Auger Microscopy and x-ray Microanalysis”, A. G. Nassiopoulou, N. Glezos and E. Valamontes, Proc. ECASIA 1991, Budapest, Hungary, (1991)
- C1.62** “Point-to-point resolution in X-ray Microanalysis of thin coatings in the energy range 20-100keV”, A. G. Nassiopoulou and E. Valamontes, Microscopy of Semiconducting Materials, Inst. Phys. Conf. Series, 117(2) (1991) 75
- C1.63** “Monte-Carlo Calculations of the Spatial Resolution in X-ray Microanalysis of thin overlayers, in the Energy Range 20-100 keV”, A. G. Nassiopoulou and E. Valamontes, Microbeam Analysis, vol.1 (1990) 161
- C1.64** “Experimental Determination of the Total Enhancement Factor in X-ray Microanalysis of Thin Overlayers”, A. G. Nassiopoulou, E. Valamontes, A. Travlos, C. Tsamis, Proc. 12th Int. Congr. Elec. Micr., 218, (1990)
- C1.65** “Surface Microanalysis with a variable information depth. Study of Silicon Oxides on Silicon”, A. G. Nassiopoulou and J. Cazaux, Microscopy of Semiconducting Materials, Inst. Phys. Conf. Ser. 100(2) (1989) 93
- C1.66** “Backscattering factor for EPMA analysis of stratified materials: Experiments and Monte-Carlo calculations”, J. Cazaux, O. Jbara, A. G. Nassiopoulou, E. Valamontes, Proc. 12th Inter. Congr. on X-ray Opt. and Micr., 201,(1989)
- C1.67** “Scanning X-ray Microfluorescence in a SEM for the Analysis of very thin overlayers”, E. Valamontes, A. G. Nassiopoulou, Proceed. of the III Balkan Congress on Electron Microscopy, Athens, Greece (1989), p.277
- C1.68** “Use of the SEM for thickness measurements, with a submicron resolution, of thin silicides grown on Silicon”, A. G. Nassiopoulou, T. Travlos, D. Tambouris, E. Valamontes, Proceed. of III Balkan Congress on Electron Microscopy, Athens-Greece, (1989), p.285
- C1.69** “Backscattering and X-ray induced correction factors for EPMA (EDX) Analysis of stratified materials”, A. G. Nassiopoulou, E. Valamontes, Proceed. of III Balkan Congress on Electron Microscopy, Athens, Greece, (1989),p.188
- C1.70** “Film thickness distribution and thickness measurements of buried layers using the Electron Probe Microanalysis Technique”, A. G. Nassiopoulou, E. Valamontes, Int. Conf. Ser. No 93: Vol. 2, Chap.4 (1988) 157
- C1.71** “Spectroscopie d'excitation des niveaux electroniques profonds par reflexion d' electrons lents sur des surfaces”, A. G. Nassiopoulou, X. Thomas, J. Cazaux, Journal de Microscopie et Spectr. Electroniques, Vol.9 (1984) 23

- C1.72** “Un appareil d'analyse des surfaces par spectroscopies de seuil”, A. G. Nassiopoulou, J. Cazaux, Journ. Micr. Spectr. Electr., Vol.7 (1982) 14a
- C1.73** “Microanalyse par Spectroscopie Auger Induite par les rayons X (raies caracteristiques et radiation Continue)”, D. Gramari, A. G. Nassiopoulou, J. Cazaux, Journ. Micr. Spectr. Electroniques, Vol.7 (1982) 14a
- C1.74** “Utilization of a simple cylindrical ion trap as a low-cost spectrometer or analyzer-element in an He-leak-detector”, A. G. Nassiopoulou, P.A. Moller, Proceeding of the 8th Inter. Vacuum Congress, Vol.III (1980) 211-214

## **C2. Greek Conference Proceedings**

- C2.1** “Ultrafast phenomena in ultrathin polycrystalline silicon films”, E. Lioudakis, L. Loumakos, A. G. Nassiopoulou and A. Othonos, XXII Panhellenic Solid State and Material Science conference, University of Patra -Greece, Proceedings conference (2008)
- C2.2** “Growth of erbium silicide films on (100) silicon as characterized by electron microscopy and diffraction”, N. Frangis, J. Van Larduyt, G. Kaltsas, A. Travlos and A. G. Nassiopoulou, Proceed. 5th Congress of the Greek Society of Electron Microscopy, Xanthi, Greece 9-11 May 1997, p.33 (1997)
- C2.3** «Πυριτίδια επαφών σε κυκλώματα VLSI πυριτίου. Τροποποιημένη διαδικασία ανάπτυξης του πυριτιδίου του Ti για ρηχές επαφές και υπομικρονικά κυκλώματα», Π. Ρέββα, Α. Καστανάς, Α. Νασιοπούλου, Πρακτικά 7ο Πανελλήνιο Συνέδριο Φυσικής, Ηράκλειο Κρήτης, 4-7 Απριλίου 1996
- C2.4** «Διατάξεις εκπομπής φωτός βασισμένες σε κβαντικά νήματα και νανοκρυσταλλίτες πυριτίου», Α. Νασιοπούλου, Σ. Γρηγορόπουλος, Δ. Παπαδημητρίου, Β. Ιωάννου-Σουγλερίδης, Πρακτικά XII Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, Ηράκλειο 15-18/9 1996
- C2.5** «Μελέτη RAMAN και φωταύγειας πορώδους πυριτίου σε υψηλές υδροστατικές πιέσεις», Δ. Παπαδημητρίου, Γ. Σ. Ράπτης, Α. Γ. Νασιοπούλου, Γ. Καλτσάς, Πρακτικά XII Πανελληνίου, Συνεδρίου Φυσικής Στερεάς Κατάστασης, Ηράκλειο 15-18 /9 1996
- C2.6** «Υπομικρονικές δομές πορώδους πυριτίου», Σ. Γρηγορόπουλος, Α. Γ. Νασιοπούλου, Δ. Παπαδημητρίου, Πρακτικά X Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης (1994) σελ. 259
- C2.7** «Υψηλά ανισοτροπική εγχάραξη υπομικρονικών δομών πυριτίου με την χρήση ενεργών ιόντων φθοριούχων αερίων σε θερμοκρασία περιβάλλοντος», Σ. Γρηγορόπουλος, Ε. Γογγολίδης, Α. Γ. Νασιοπούλου Πρακτικά X Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, (1994) σελ. 259
- C2.8** «Μελέτη της διεπαφής λεπτών υμενίων πυριτιδίων του Ti σε Si, που παρασκευάζονται με εναλλάξ στρώματα Πυριτίου-Τιτανίου και ανόπτηση», Π. Ρέββα, Α. Νασιοπούλου και Α. Τραυλός Πρακτικά IX Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, 1993, σελ 228

- C2.9** «Πυριτίδια του τανταλίου και εναλλάξ εναπόθεση Ta/Si και ανόπτηση σε υψηλή θερμοκρασία», Α. Γ. Νασιοπούλου, Α. Τραυλός Π. Αλουπογιάννης, Σ. Γεωργά, Χ. Κροντηράς, Ν. Ξανθόπουλος, Πρακτικά ΙΧ Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, 1993, σελ 212
- C2.10** «Πυριτίδια του Τι από πολυστρωματικά υμένια εναλλάξ α-Si/Ti. Χαρακτηρισμός με Ηλεκτρονική Μικροσκοπία, φασματοσκοπική ελλειψομετρία και ηλεκτρικές μετρήσεις" Α. Γ. Νασιοπούλου, Δ. Ταμπούρης, Σ. Λογοθετίδης, Φράγκης, Χ. Κροντηράς, Σ. Γεωργά, Ν. Ξανθόπουλος, Πρακτικά VIII Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, 1992, 137
- C2.11** "Διακριτική ικανότητα της Μικροανάλυσης X λεπτών υμενίων σε στερεό υπόστρωμα και λεπτών μη υποβασταζόμενων υμενίων", Α. Γ. Νασιοπούλου και Ε. Βαλαμόντες, Πρακτικά VII Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης ,(1991) 497
- C2.12** «Εφαρμογή των εξισώσεων μεταφοράς ηλεκτρονίων στην Μικροανάλυση X λεπτών υμενίων σε υπόστρωμα και την μέτρηση του πάχους των υμενίων», Ν. Γλέζος, Α. Νασιοπούλου, Ε. Βαλαμόντες Πρακτικά VII Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, (1991),16
- C2.13** «Αντίδραση πολυστρωματικών υμενίων α-Si/Ti για την δημιουργία TiSi<sub>2</sub>. Εφαρμογή σε ρηχές επαφές για υπομικρονικά κυκλώματα» , Α. Νασιοπούλου, Δ. Ταμπούρης, Α. Τραυλός, Π. Αλουπογιάννης, Α. Traverse, και Ε. Τσώη, Πρακτικά VII Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, (1991) 150
- C2.14** «Ανάπτυξη πυριτιδίων του Τι με in-situ ταχεία ανόπτηση στο εσωτερικό Ηλεκτρονικού Μικροσκοπίου Σάρωσης», Α. Τραυλός, Α. Γ. Νασιοπούλου, Δ. Ταμπούρης, Πρακτικά VI Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, Κρήτη, Σεπτ. 1990
- C2.15** «Η τεχνική της Μικροανάλυσης με Ηλεκτρόνια (EPMA) για την μέτρηση του πάχους λεπτών υμενίων», Α. Γ. Νασιοπούλου, Ε. Βαλαμόντες, Πρακτικά Δ' Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης., 1988, σελ.246
- C2.16** «Προσδιορισμός πάχους και κατανομής πάχους λεπτών υμενίων θαμμένων κάτω από άλλο υμένιο», Ε. Βαλαμόντες, Α. Νασιοπούλου, Α. Τραυλός, Πρακτικά IV Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης 1988, σελ.264
- C2.17** «Ανώμαλη συμπεριφορά των στατικών χαρακτηριστικών των MOFSET n και p καναλιού στην περιοχή θερμοκρασιών 4.2K-14K», Α. Γ. Νασιοπούλου, Ε. Ροκοφύλου, Δ. Τσαμάκης, F.Balestra Πρακτικά IV Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης., 1988, σελ.22
- C2.18** «Μικροανάλυση X λεπτών υμενίων σε στερεό υπόστρωμα. ολικός συντελεστής διόρθωσης και διακριτική ικανότητα», Ε. Βαλαμόντες, Α. Γ. Νασιοπούλου, Πρακτικά VI Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, Κρήτη, Σεπτ. 90
- C2.19** «Διακριτική ικανότητα της φασματοσκοπίας Auger για υψηλή ενέργεια της προσπίπτουσας δέσμης». Ν. Γλέζος, Α. Γ. Νασιοπούλου. Πρακτικά VI Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης, Κρήτη, Σεπτ. 90
- C2.20** «Συμπεριφορά των TMOS σε θερμοκρασίες μικρότερες των 20K», Ε. Βαλαμόντες, Α. Γ. Νασιοπούλου, Ε. Ροκοφύλου, Δ. Τσαμάκης, F. Balestra, G. Ghibaido, Πρακτικά Γ' Πανελληνίου Συνεδρίου Φυσικής Στερεάς Κατάστασης., 1987
- C2.21** «Πειραματική διάταξη που καθιστά μικροαναλυτικές τις φασματοσκοπίες φωτοηλεκτρονίων (XPS) και ηλεκτρονίων Auger με ιονισμό από ακτίνες X (XAES)», Α. Γ. Νασιοπούλου και J. Cazaux, Πρακτικά Δ' Πανελληνίου Συνεδρίου Φυσικής, 1986

**C2.22** «Μικροανάλυση επιφανειών και παρατήρηση μη διπολικών μεταπτώσεων με τη φασματοσκοπία απωλειών ενέργεια βραδέων ηλεκτρονίων», Α. Γ. Νασιοπούλου, Πρακτικά Β' Πανελλήνιου Συνεδρίου Φυσικής Στερεάς Κατάστασης, 1986,60